CRMKGL0604A

N-Channel 60V, 3.8mΩ Typ. Power MOSFET

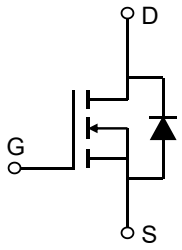
Description

Features

- 60V, 91A

  $R_{DS(ON)}$ Typ = 3.8mΩ @ V_{GS} = 10V

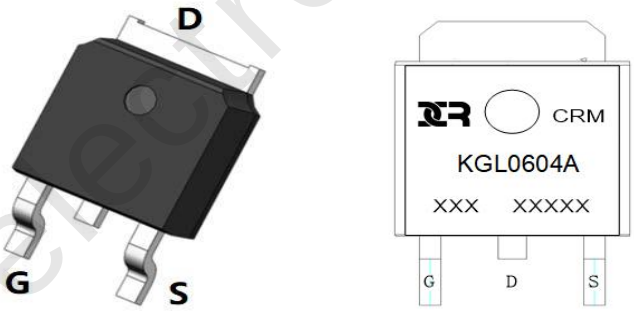
  $R_{DS(ON)}$ Typ = 5mΩ @ V_{GS} = 4.5V
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔVds TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMKGL0604A	CRMKGL0604A	TO-252-3L	TAPING	13"	2500	25000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		60	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	91	A
		T_C = 100°C	54.6	A
I_{DM}	Pulsed Drain Current (1)		364	A
E_{AS}	Single Pulsed Avalanche Energy (2)		127	mJ
P_D	Power Dissipation	T_C = 25°C	69.4	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.8	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.2	1.7	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 20A	-	3.8	4.9	mΩ
		V_{GS} = 4.5V, I_D = 10A	-	5	6.5	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz	-	2000	-	pF
C_{oss}	Output Capacitance		-	660	-	pF
C_{rss}	Reverse Transfer Capacitance		-	28	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 30V, I_D = 20A	-	35	-	nC
Q_{gs}	Gate Source Charge		-	10	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 30V, I_D= 20A, R_{GEN} = 4.5Ω	-	12	-	ns
t_r	Turn-On Rise Time		-	34	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	25	-	ns
t_f	Turn-Off Fall Time		-	30	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	91	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	364	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	-	38	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	23	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=30V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=22.5A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

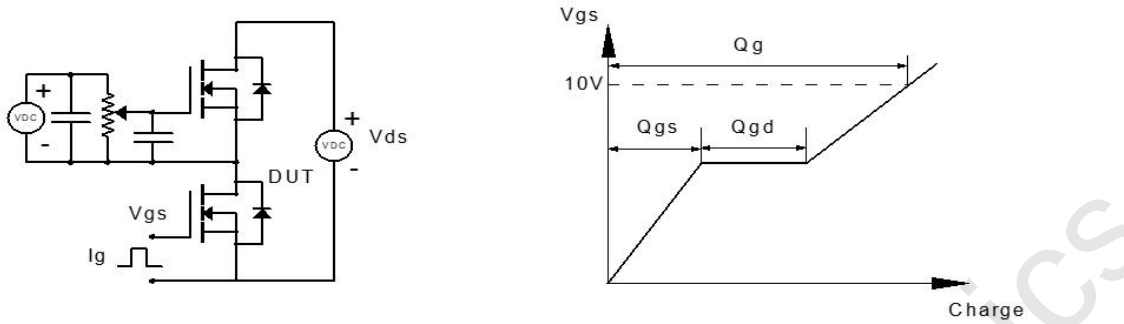


Figure 1: Gate Charge Test Circuit & Waveform

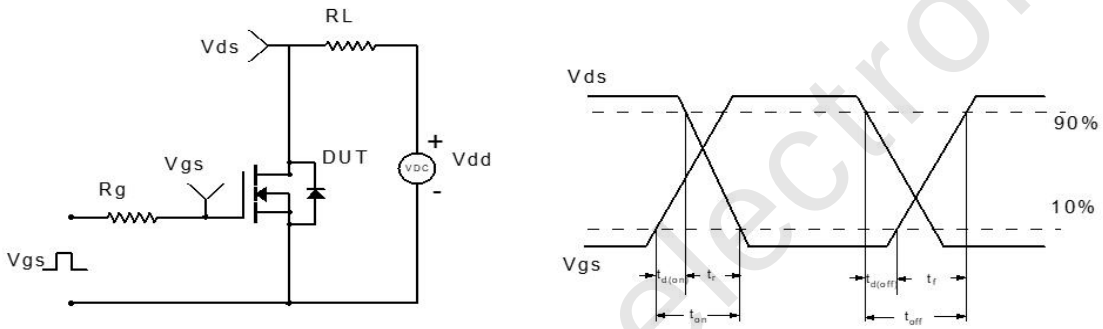


Figure 2: Resistive Switching Test Circuit & Waveform

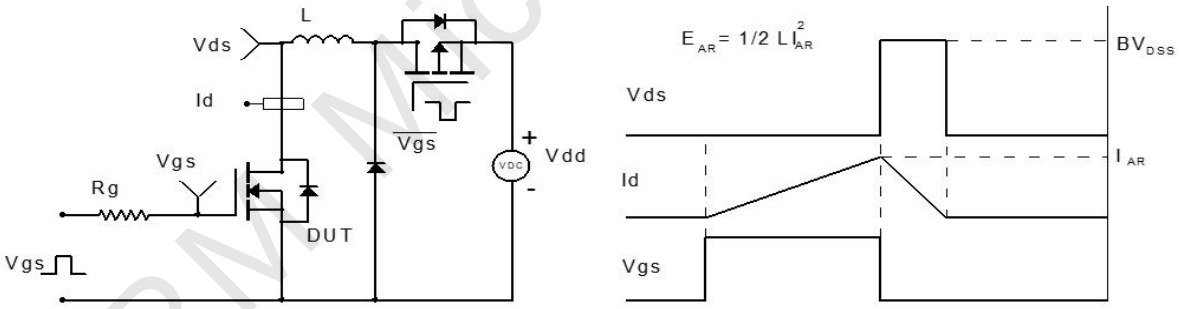


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

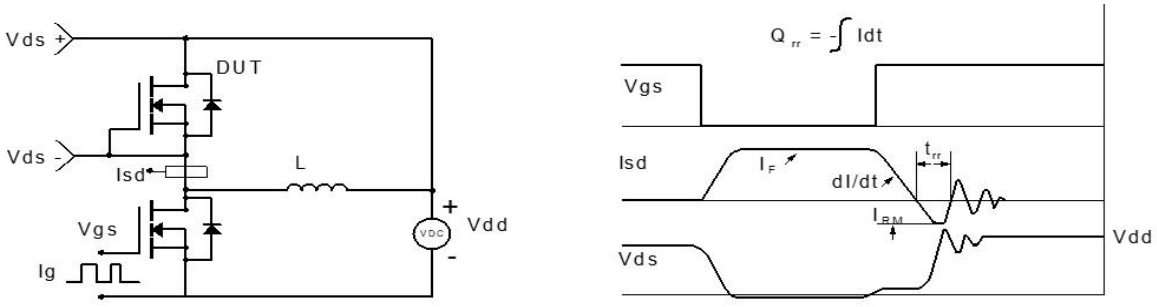
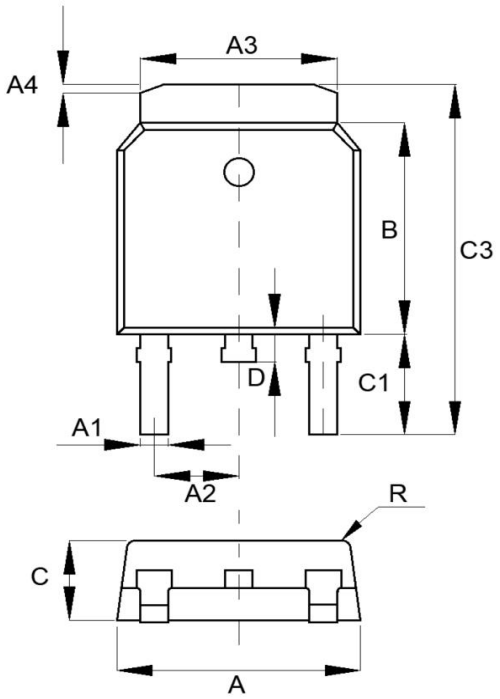
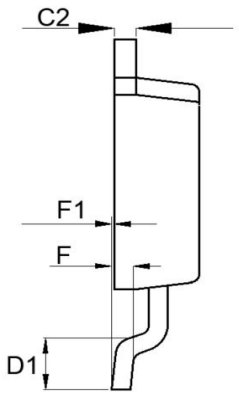


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)





SYMBOL	MIN	NOM	MAX
A	6.550	6.600	6.650
A1	0.640	0.690	0.740
A2	——	2.286	——
A3	5.234	5.334	5.434
A4	0.070	0.270	0.470
B	6.050	6.100	6.150
C	2.250	2.300	2.350
C1	2.650	2.780	2.950
C2	0.504	0.508	0.510
C3	9.750	9.850	10.00
D	0.700	0.800	0.900
D1	1.400	1.500	1.600
F	——	0.508	——
F1	0	0.050	0.100
R	——	0.250	——

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